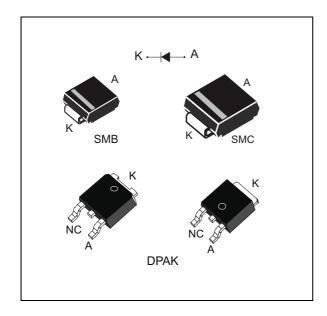
STTH4R02



Ultrafast recovery diode

Datasheet - production data



Symbol	Value
I _{F(AV)}	4 A
V_{RRM}	200 V
V _F (typ)	0.76 V
T _j (max)	175 °C
t _{rr} (typ)	16 ns

Table 1. Device summary

The STTH4R02 uses ST's new 200 V planar Pt doping technology, and it is specially suited for switching mode base drive and transistor circuits. Packaged in DPAK, SMB and SMC, this device is intended for use in low voltage, high frequency inverters, freewheeling and polarity protection.

Description

Features

- · Negligible switching losses
- High junction temperature
- Very low conduction losses
- Low forward and reverse recovery times
- ECOPACK[®]2 compliant component for DPAK on demand

Characteristics STTH4R02

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parai	Value	Unit		
V_{RRM}	Repetitive peak reverse voltage	Repetitive peak reverse voltage			V
1	Forward rms current	DPAK		10	Α
I _F (RMS)	P(RMS)	SMB / SMC		70	^
1	Average forward current,	DPAK	T _c = 160 °C	4	Α
I _{F(AV)}	$\delta = 0.5$, square wave	SMB / SMC	T _L = 95 °C	4	A
I _{FSM}	Surge non repetitive forward current t _p = 10 ms sinusoidal			70	Α
T _{stg}	Storage temperature range			-65 to +175	°C
T _j	Maximum operating junction temperature			175	°C

Table 3. Thermal parameters

Symbol	Parameter	Max. value	Unit	
R _{th(j-c)}	Junction to case	DPAK	3.5	°C/W
R _{th(j-l)}	Junction to lead	SMB / SMC	20	C/VV

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V- - V	-		3	шА
'R'	Reverse leakage current	T _j = 125 °C	$V_R = V_{RRM}$	ı	2	20	μA
	Forward voltage drop	T _i = 25 °C	I _F = 12 A	-	1.15	1.25	
V _F ⁽²⁾		1 _j = 25 C	Ι _ 4 Δ	-	0.95	1.05	V
		T _j = 150 °C	I _F = 4 A	-	0.76	0.83	

^{1.} Pulse test: t_p = 5 ms, δ < 2%

To evaluate the conduction losses, use the following equation:

$$P = 0.67 \times I_{F(AV)} + 0.04 \times I_{F}^{2}_{(RMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

STTH4R02 Characteristics

Table 5. Dynamic electrical characteristics

Symbol	Parameter		Tests conditions	Min.	Тур.	Max.	Unit
+	. Downson time T		$I_F = 1 \text{ A}$ $dI_F/dt = -50 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$	-	24	30	ns
t _{rr}	Reverse recovery time	T _j = 25 °C	$I_F = 1 \text{ A}$ $dI_F/dt = -100 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$	-	16	20	115
I _{RM}	Reverse recovery current	T _j = 125 °C	$I_F = 4 \text{ A}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	4.4	5.5	А
t _{fr}	Forward recovery time	T _j = 25 °C	$I_F = 4 \text{ A}$ $dI_F/dt = 50 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$	-	80		ns
V _{FP}	Forward recovery voltage	•	I _F = 4 A dI _F /dt = 50 A/μs	-	1.6		V

Characteristics STTH4R02

Figure 1. Peak current versus duty cycle 50 45 40 δ= tp/T 35 30 25 P = 2 W 20 15 10 δ 5 0 0.2 0.3 0.4 0.6 0.7 0.5 8.0 0.9

Figure 2. Forward voltage drop versus forward current (typical values) $I_{\mathsf{F}}(\mathsf{A})$ 100 75 T = 150 °C 50 25 0 0.0 1.0 0.5 1.5 2.0 2.5 3.0 3.5

Figure 3. Forward voltage drop versus forward current (maximum values)

1.5

Figure 5. Relative variation of thermal

impedance, junction to ambient, versus pulse

2.0

2.5

3.0

3.5

Figure 4. Relative variation of thermal impedance, junction to case, versus pulse duration

2th(j-c)/Rth(j-c)
DPAK
Single pulse

1.E-03
1.E-02
1.E-01
1.E+00

duration (SMB) $Z_{th(j-a)}/R_{th(j-a)}$ 1.0 0.9 SMB $S_{CU} = 1 \text{ cm}^2$ 0.8 0.7 0.6 0.5 0.4 0.3 0.2 0.1 0.0 1.E+00 1.E+01 1.E+02 1.E-01 1.E+03

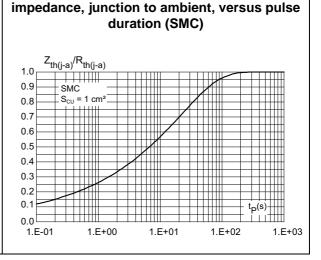


Figure 6. Relative variation of thermal

10

0.0

0.5

1.0

STTH4R02 **Characteristics**

1000

Figure 7. Junction capacitance versus reverse applied voltage (typical values) 100 C(pF)

 $V_{R}(V)$

10

1

Figure 8. Reverse recovery charges versus dl_F/dt (typical values) $Q_{rr}(nC)$ I_F = 4 A V_R= 160 V 100 80 60 40 20 $dI_F/dt (A/\mu s)$ 0 100 150 200 250 300 350 400 450 500

(typical values) t_{rr}(ns) 80 70 60 50

Figure 9. Reverse recovery time versus dl_F/dt

40 30 20 10 dl_F/dt (A/μs) 0 10 100 1000

versus dl_F/dt (typical values) I_{RM}(A) 10 F= 160 \ 8 6 $dI_F/dt (A/\mu s)$ 0 250 300 350

Figure 10. Peak reverse recovery current

temperature (reference: T_i = 125 °C) 1.0 0.8 0.6 0.4 T_i (°C)_ 0.0 100 150

Figure 11. Dynamic parameters versus junction

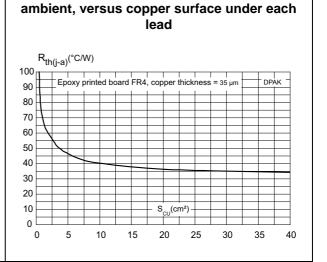
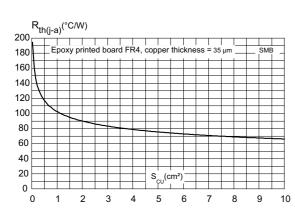


Figure 12. Thermal resistance, junction to

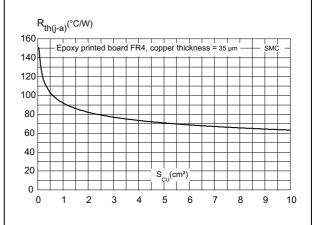
Characteristics STTH4R02

Figure 13. Thermal resistance, junction to ambient, versus copper surface under each lead



6/14

Figure 14. Thermal resistance, junction to ambient, versus copper surface under tab



2 **Package information**

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)
- Band indicates cathode

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 **DPAK** package information

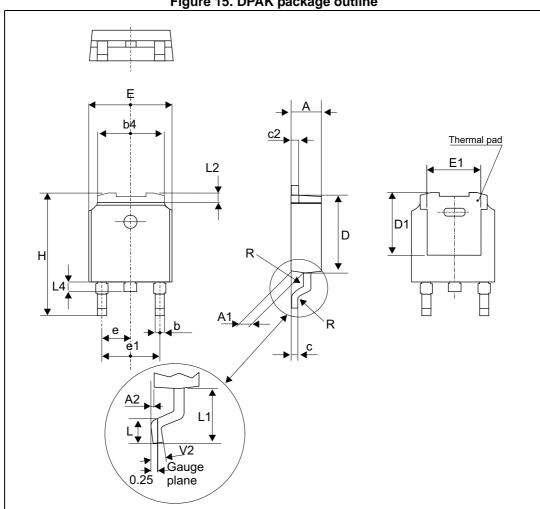


Figure 15. DPAK package outline

Note:

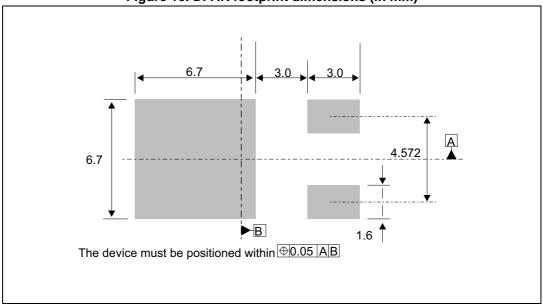
This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Package information STTH4R02

Table 6. DPAK package mechanical data

				Dimensions		
Ref.		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	2.18		2.40	0.085		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
b	0.64		0.90	0.025		0.035
b4	4.95		5.46	0.194		0.214
С	0.46		0.61	0.018		0.024
c2	0.46		0.60	0.018		0.023
D	5.97		6.22	0.235		0.244
D1	4.95		5.60	0.194		0.220
Е	6.35		6.73	0.250		0.264
E1	4.32		5.50	0.170		0.216
е		2.28			0.090	
e1	4.40		4.70	0.173		0.185
Н	9.35		10.40	0.368		0.409
L	1.00		1.78	0.039		0.070
L2			1.27			0.050
L4	0.60		1.02	0.023		0.040
V2	-8°		+8°	-8°		8°

Figure 16. DPAK footprint dimensions (in mm)



2.2 SMB package information

E1

A1

A2

Figure 17. SMB package outline

Table 7. SMB package mechanical data

		Dimer	nsions	
Ref.	Millim	neters	Inc	hes
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
С	0.15	0.40	0.006	0.016
D	3.30	3.95	0.130	0.156
E	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
L	0.75	1.50	0.030	0.059

Package information STTH4R02

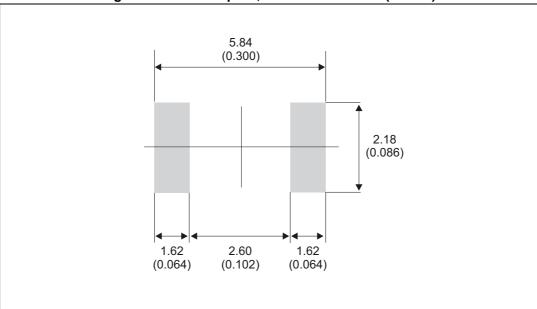


Figure 18. SMB footprint, dimensions in mm (inches)

2.3 SMC package information

Figure 19. SMC package outline

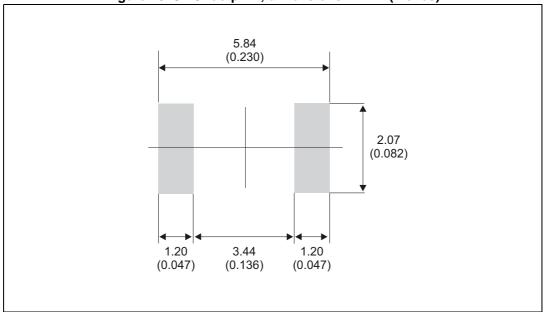
Package information STTH4R02

Table 8. SMC package mechanical data

	Dimensions				
Ref.	Millim	eters	Inc	hes	
	Min.	Max.	Min.	Max.	
A1	1.90	2.45	0.075	0.096	
A2	0.05	0.20	0.002	0.008	
b ⁽¹⁾	2.90	3.20	0.114	0.126	
c ⁽¹⁾	0.15	0.40	0.006	0.016	
D	5.55	6.25	0.218	0.246	
E	7.75	8.15	0.305	0.321	
E1	6.60	7.15	0.260	0.281	
E2	4.40	4.70	0.173	0.185	
L	0.75	1.50	0.030	0.059	

^{1.} Dimensions b and c apply to plated leads

Figure 20. SMC footprint, dimensions in mm (inches)



3 Ordering information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH4R02B-TR	STTH 4R02	DPAK	0.32 g	2500	Tape and reel
STTH4R02U	4R2U	SMB	0.110 g	2500	Tape and reel
STTH4R02S	4R2S	SMC	0.243 g	2500	Tape and reel

4 Revision history

Table 10. Document revision history

Date	Revision	Changes
03-May-2006	1	First issue.
10-Oct-2006	Oct-2006 2 Added SMC package	
13-Apr-2010	3	Updated ECOPACK statement. Updated dimensions tables for SMB and SMC.
01-Jul-2010	4	Separated junction to lead values from junction to case values in <i>Table 3</i> .
20-Nov-2014	5	Removed TO-220AC, TO-220FPAC and DO-201AB package informations.
02-Nov-2016	6	Updated DPAK package information and reformatted to current standard.

IMPORTANT NOTICE - PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2016 STMicroelectronics – All rights reserved